Albert Baca

List of Publications by Year in descending order

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27	699	471061 17	552369 26
papers	citations	h-index	g-index

27	27	27	574
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High-Al-content heterostructures and devices. Semiconductors and Semimetals, 2021, , 191-222.	0.4	0
2	Thermal Conductivity of Î²-Phase Ga₂O₃ and (Al_xGa_{1â€“}_x)₂O₃ Heteroepitaxial Thin Films. ACS Applied Materials & Interfaces, 2021, 13, 38477-38490.	4.0	24
3	Interdependence of Electronic and Thermal Transport in Al_xGa_{1â€“x}N Channel HEMTs. IEEE Electron Device Letters, 2020, 41, 461-464.	2.2	15
4	Al-rich AlGaN based transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	33
5	High temperature operation to 500â€‰Â°C of AlGaN graded polarization-doped field-effect transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, .	0.6	2
6	Extreme Temperature Operation of Ultra-Wide Bandgap AlGaN High Electron Mobility Transistors. IEEE Transactions on Semiconductor Manufacturing, 2019, 32, 473-477.	1.4	19
7	Saturation Velocity Measurement of Al0.7Ga0.3N-Channel High Electron Mobility Transistors. Journal of Electronic Materials, 2019, 48, 5581-5585.	1.0	7
8	Multidimensional thermal analysis of an ultrawide bandgap AlGaN channel high electron mobility transistor. Applied Physics Letters, 2019, 115, .	1.5	30
9	III-Nitride ultra-wide-bandgap electronic devices. Semiconductors and Semimetals, 2019, 102, 397-416.	0.4	3
10	High-frequency, high-power performance of AlGaN-channel high-electron-mobility transistors: an RF simulation study. Japanese Journal of Applied Physics, 2019, 58, SCCD04.	0.8	11
11	Operation Up to 500 Â°C of Al_{0.85}Ga_{0.15}N/Al_{0.7}Ga_{0.3}N High Electron Mobility Transistors. IEEE Journal of the Electron Devices Society, 2019, 7, 444-452.	1.2	36
12	Enhancement-mode AlGaN channel high electron mobility transistor enabled by p-AlGaN gate. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, .	0.6	16
13	Enhancement-mode Al0.85Ga0.15N/Al0.7Ga0.3N high electron mobility transistor with fluorine treatment. Applied Physics Letters, 2019, 114, .	1.5	17
14	AlGaN polarization-doped field effect transistor with compositionally graded channel from Al0.6Ga0.4N to AlN. Applied Physics Letters, 2019, 114, .	1.5	22
15	Demonstration of a 9â€¯kV reverse breakdown and 59â€¯mÎ©-cm2 specific on-resistance AlGaN/GaN Schottky barrier diode. Solid-State Electronics, 2019, 151, 47-51.	0.8	11
16	Radiation Response of AlGaN-Channel HEMTs. IEEE Transactions on Nuclear Science, 2019, 66, 344-351.	1.2	21
17	RF Performance of Al0.85Ga0.15N/Al0.70Ga0.30N High Electron Mobility Transistors with 80 nm Gates. IEEE Electron Device Letters, 2018, , 1-1.	2.2	27
18	Ultra-wide band gap AlGaN polarization-doped field effect transistor. Japanese Journal of Applied Physics, 2018, 57, 074103.	0.8	17

#	Article	IF	Citations
19	Reviewâ€"Ultra-Wide-Bandgap AlGaN Power Electronic Devices. ECS Journal of Solid State Science and Technology, 2017, 6, Q3061-Q3066.	0.9	104
20	Ohmic contacts to Alâ€rich AlGaN heterostructures. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600842.	0.8	36
21	Al_{0.85}Ga_{0.15}N/Al_{0.70}Ga_{0.30}N High Electron Mobility Transistors with Schottky Gates and Large On/Off Current Ratio over Temperature. ECS Journal of Solid State Science and Technology, 2017, 6, Q161-Q165.	0.9	36
22	High Temperature Operation of Al_{0.45}Ga_{0.55}N/Al_{0.30}Ga_{0.70}N High Electron Mobility Transistors. ECS Journal of Solid State Science and Technology, 2017, 6, S3010-S3013.	0.9	26
23	Planar Ohmic Contacts to Al_{0.45}Ga_{0.55}N/Al_{0.3}Ga_{0.7}N High Electron Mobility Transistors. ECS Journal of Solid State Science and Technology, 2017, 6, S3067-S3071.	0.9	27
24	Analysis of 2D Transport and Performance Characteristics for Lateral Power Devices Based on AlGaN Alloys. ECS Journal of Solid State Science and Technology, 2017, 6, S3114-S3118.	0.9	36
25	An AlN/Al0.85Ga0.15N high electron mobility transistor. Applied Physics Letters, 2016, 109, .	1.5	108
26	Spectroscopic investigations of band offsets of MgO|AlxGa1-xN epitaxial heterostructures with varying AlN content. Applied Physics Letters, 2015, 107, .	1.5	12
27	Inductively Coupled High-Density Plasma-Induced Etch Damage of GaN MESFETs. Materials Research Society Symposia Proceedings, 2000, 622, 751.	0.1	3